

9. (Amended) A nitride semiconductor laser comprising

a GaN substrate having a single-crystal GaN layer at least on its surface and

device-forming layers made of nitride semiconductor that are formed on said

GaN substrate and are devoid of small cracks,

wherein said single-crystal GaN layer is formed through a lateral-growth process;

and

said device-forming layer contacting said GaN substrate is made of

$\text{Al}_a\text{Ga}_{1-a}\text{N}$ ($0 < a \leq 1$) and has a coefficient of thermal expansion less than that of the GaN

substrate thereby providing compression strain on the device-forming layer.